Randy L. Hoffman, et al.

SEMICONDUCTOR DEVICE

Herewith

Inventor(s):

Filing Date:

Title:

Application No.:

PATENT APPLICATION

ATTORNEY DOCKET NO. 200316548-1

Confirmation No.:

Group Art Unit:

Examiner:

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents PO Box 1450
Alexandria, VA 22313-1450 INFORMATION DISCLOSURE STATEMENT
Sir:
This Information Disclosure Statement is submitted:
 (x) under 37 CFR 1.97(b), or (Within three months of filing national application; or date of entry of national application; or before mailing date of first office action on the merits; whichever occurs last)
 () under 37 CFR 1.97(c) together with either a: () Statement under 37 CFR 1.97(e), or () a \$180.00 fee under 37 CFR 1.17(p), or (After the CFR 1.97 (b) time period, but before final action or notice of allowance, whichever occurs first)
 () under 37 CFR 1.97 (d) together with a: () Statement under 37 CFR 1.97(e)(1) or (2), and () a \$180.00 fee set forth in 37 CFR 1.17(p). (Filed after final action, a notice of allowance, on or before payment of the issue fee)
Please charge to Deposit Account 08-2025 the sum of \$0.00 . At any time during the pendency of this application, please charge any fees required or credit any overpayment to Deposit Account 08-2025 pursuant to 37 CFR 1.25.
(X) Applicant(s) submit herewith Form PTO 1449 - Information Disclosure Statement together with any required copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s) may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 CFR 1.56.
() A concise explanation of the relevance of foreign language patents, foreign language publications

and other foreign language information listed on PTO Form 1449, as presently understood by the individuals(s) designated in 37 CFR 1.56 (c) most knowledgeable about the content is given on the attached sheet, or where a foreign language patent is cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action which indicates the degree of relevance found by the foreign office is listed on form PTO

It is requested that the information disclosed herein be made of record in this application.

Respectfully submitted,

Hoffman, et∕aj Randy L

Edward J. Brooks III^b

Attorney/Agent for Applicant(s)

Reg. No. 40,925

Date: 03/12/2004

Telephone No.: (612) 659-9340

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Typed Name: Sarah L. Reinhard

Commissioner

1449 and is enclosed herewith.

"Express Mail" label no. EV372029214US

Date of Deposit 03/12/2004

I hereby certify that this is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to:

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Sheet 1 of 6

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